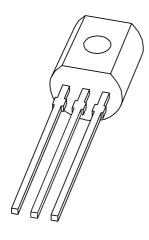
DISCRETE SEMICONDUCTORS

DATA SHEET



BSR52NPN Darlington transistor

Product data sheet Supersedes data of 1999 Apr 26 2004 Nov 11



NPN Darlington transistor

BSR52

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

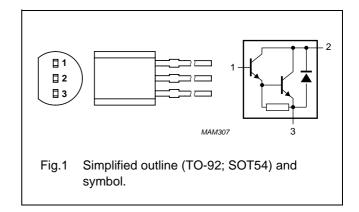
• Industrial high gain amplification.

DESCRIPTION

NPN Darlington transistor in a TO-92; SOT54 plastic package. PNP complement: BSR62.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter



ORDERING INFORMATION

TYPE NUMBER		PACKAGE				
TIPE NOMBER	NAME DESCRIPTION VERSION					
BSR52	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	90	V
V _{CES}	collector-emitter voltage	V _{BE} = 0 V	_	80	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	1	А
I _{CM}	peak collector current		_	2	А
I _B	base current (DC)		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	830	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN Darlington transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	150	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

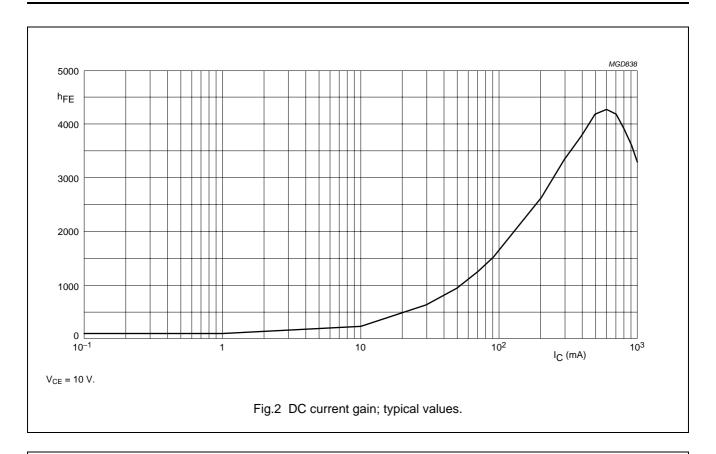
CHARACTERISTICS

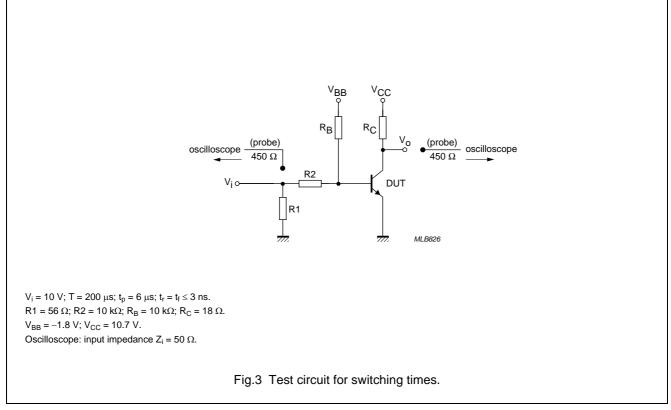
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
I _{CES}	collector-base cut-off current	ctor-base cut-off current $V_{BE} = 0 \text{ V}; V_{CE} = 80 \text{ V}$		_	50	nA	
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$	_	_	50	nA	
h _{FE}	DC current gain	V _{CE} = 10 V; see Fig.2					
		I _C = 150 mA	1000	_	_		
		I _C = 500 mA	2000	_	_		
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 0.5 mA	_	_	1.3	V	
		I _C = 1 A; I _B = 4 mA	_	_	1.6	V	
V _{BEsat}	base-emitter saturation voltage	I _C = 0.5 A; I _B = 0.5 mA	_	_	1.9	V	
		I _C = 1 A; I _B = 4 mA	_	_	2.2	V	
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 500 \text{ mA;}$ f = 100 MHz	-	200	_	MHz	
Switching t	Switching times (between 10% and 90% levels); see Fig.3						
t _{on}	turn-on time	I _{Con} = 500 mA; I _{Bon} = 0.5 mA;	_	-	500	ns	
t _{off}	turn-off time	$I_{Boff} = -0.5 \text{ mA}$	_	_	1300	ns	

NPN Darlington transistor

BSR52





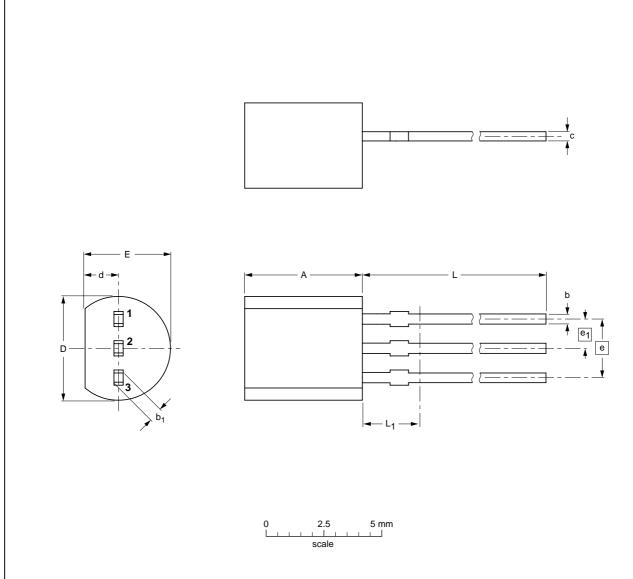
NPN Darlington transistor

BSR52

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			04-06-28 04-11-16

NPN Darlington transistor

BSR52

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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